

20V N-Channel MOSFET



SOT-23

Pin Definition:

- 1. Gate
- 2. Source
- 3. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
20	33 @ V _{GS} = 4.5V	4.9
	40 @ V _{GS} = 2.5V	4.4
	100 @ V _{GS} = 1.8V	2.9

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

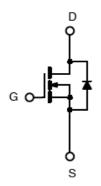
- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM2314CX RFG	SOT-23	3Kpcs / 7" Reel

Note: "G" denotes Halogen Free Product.

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	20	V	
Gate-Source Voltage		V_{GS}	±12	V	
Continuous Drain Current, V _{GS} @4.5V.		I _D	4.9	А	
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	15	А	
Continuous Source Current (Diode Conduc	ction) ^{a,b}	I _S	1.0	А	
Mariana Barra Biasinatian	Ta = 25°C	5	1.25	10/	
Maximum Power Dissipation	Ta = 75° C P_D 0.8		0.8	W	
Operating Junction Temperature		T _J +150		°C	
Operating Junction and Storage Temperate	Operating Junction and Storage Temperature Range		-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ _{JC}	75	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	120	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.



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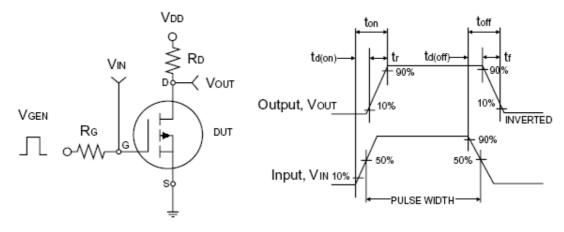


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	0.6	0.85	1.2	V
Gate Body Leakage	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$	I _{GSS}	1		±1.5	μΑ
Zero Gate Voltage Drain Current	$V_{DS} = 16V, V_{GS} = 0V$	I _{DSS}	1		1.0	μΑ
On-State Drain Current	$V_{DS} \ge 10V$, $V_{GS} = 4.5V$	I _{D(ON)}	15			Α
	$V_{GS} = 4.5V, I_D = 4.9A$		1	27	33	
Drain-Source On-State Resistance	ain-Source On-State Resistance $V_{GS} = 2.5V$, $I_D = 4.4A$ $R_{DS(ON)}$		33	40	mΩ	
	$V_{GS} = 1.8V, I_D = 2.9A$			80	100	
Forward Transconductance	$V_{DS} = 15V, I_{D} = 5.0A$	9 _{fs}		40		S
Diode Forward Voltage	$I_{S} = 1.0A, V_{GS} = 0V$	V_{SD}		0.8	1.2	V
Dynamic ^b						
Total Gate Charge	$V_{DS} = 15V, I_{D} = 5.0A$	Q_g		11	14	
Gate-Source Charge		Q_gs		1.5		nC
Gate-Drain Charge		Q_{gd}	-	2.1		
Input Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	C _{iss}	1	900		
Output Capacitance		C _{oss}		140		pF
Reverse Transfer Capacitance		C _{rss}	-	100		
Switching ^c						
Turn-On Delay Time	$V_{DD} = 10V, R_{L} = 10\Omega,$ $I_{D} = 1A, V_{GEN} = 4.5V,$ $R_{G} = 6\Omega$	t _{d(on)}	1	0.53	8.0	
Turn-On Rise Time		t _r	-	1.4	2.2	20
Turn-Off Delay Time		t _{d(off)}		13.5	20	nS
Turn-Off Fall Time		t _f		5.9	9	

Notes:

- a. pulse test: PW \leq 300 μ S, duty cycle \leq 2%
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

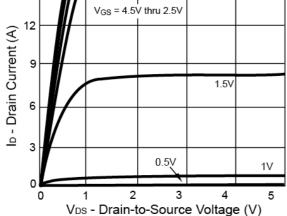
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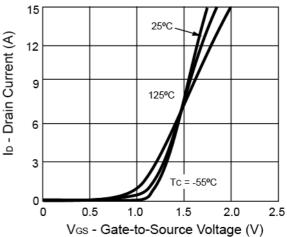
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Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

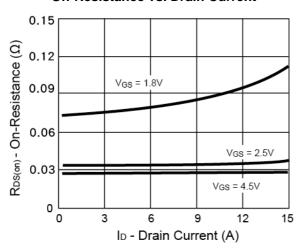
Output Characteristics



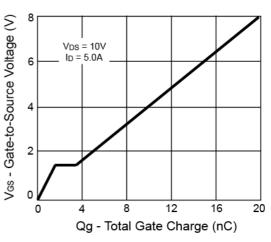
Transfer Characteristics



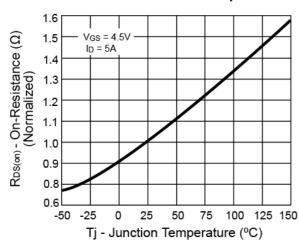
On-Resistance vs. Drain Current



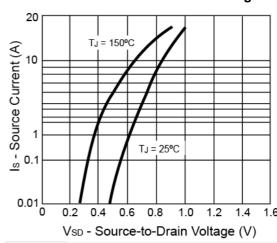
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

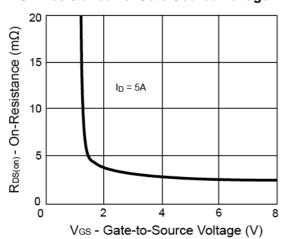


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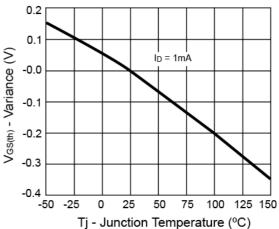


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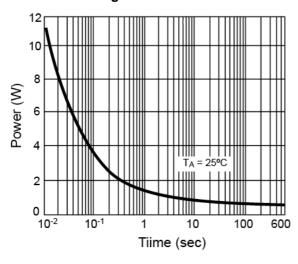
On-Resistance vs. Gate-Source Voltage



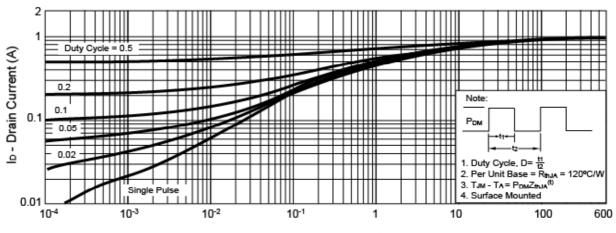
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

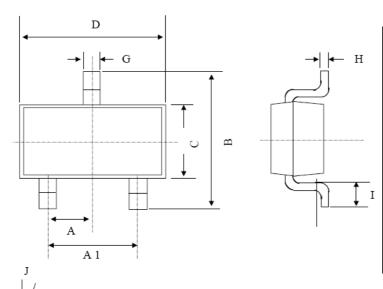






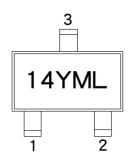


SOT-23 Mechanical Drawing



SOT-23 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	0.95	BSC	0.037 BSC		
A1	1.9	BSC	0.074	BSC	
В	2.60	3.00	0.102	0.118	
С	1.40	1.70	0.055	0.067	
D	2.80	3.10	0.110	0.122	
Е	1.00	1.30	0.039	0.051	
F	0.00	0.10	0.000	0.004	
G	0.35	0.50	0.014	0.020	
Н	0.10	0.20	0.004	0.008	
I	0.30	0.60	0.012	0.024	
J	5°	10°	5°	10°	

Marking Diagram



14 = Device Code

Y = Year Code

M = Month Code for Halogen Free Product

 \mathbf{O} =Jan \mathbf{P} =Feb \mathbf{Q} =Mar \mathbf{R} =Apr

S = May T = Jun U = Jul V = Aug

W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code



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